

Precision 5V Reference

DESCRIPTION

The RH1021-5 is a precision 5V reference with ultralow drift and noise, extremely good long term stability and almost total immunity to input voltage variations. The reference output will source and sink up to 10mA. Unique circuit design makes the RH1021-5 the first IC reference to offer ultralow drift without the use of high power onchip heaters.

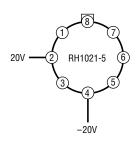
The wafer lots are processed to Linear Technology's inhouse Class S flow to yield circuits usable in stringent military applications.

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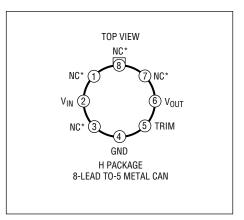
ABSOLUTE MAXIMUM RATINGS

Input Voltage 40V
Input/Output Voltage Differential
Trim Pin-to-Ground Voltage
Positive Equal to V _{OUT}
Negative20V
Output Short-Circuit Duration
V _{IN} = 35V 10 sec
V _{IN} 20V Indefinite
Operating Temperature Range55°C to 125°C
Storage Temperature Range – 65°C to 150°C
Lead Temperature (Soldering, 10 sec)300°C

BURN-IN CIRCUIT



PACKAGE/ORDER INFORMATION



* Connected internally. Do not connect external circuitry to these pins.

TABLE 1: ELECTRICAL CHARACTERISTICS (Preirradiation) (Note 8)

	PARAMETER	CONDITIONS		T _A = 25°C			SUB-	-55°C	Τ Δ	125°C	SUB-	
SYMBOL			NOTES	MIN	TYP	MAX	GROUP	MIN	TYP	MAX	GROUP	UNITS
V _{OUT}	Output Voltage	RH1021CM-5 RH1021BM-5, DM-5	1 1	4.9975 4.95		5.0025 5.05	1					V V
TCV _{OUT}	Output Voltage Temperature Coefficient	RH1021BM-5 RH1021CM-5, DM-5	2 2							5 20	2,3 2,3	ppm/°C ppm/°C
V _{OUT} V _{IN}	Line Regulation	7.2V V IN 10V 10V V IN 40V	3			12 6	1			20 10	2,3 2,3	ppm/V ppm/V
V _{OUT}	Load Regulation (Sourcing Current)	0 I _{OUT} 10mA	3			20	1			35	2,3	ppm/mA
	Load Regulation (Sinking Current)	0 I _{OUT} 10mA	3			100	1			150	2,3	ppm/mA
Is	Supply Current					1.2	1			1.5	2,3	mA
	Output Voltage Noise	0.1Hz f 10Hz 10Hz f 1kHz	4 4		3	3.5	4					μV _{P-P} μV _{RMS}
	Long Term Stability of V _{OUT}	T = 1000 Hrs Noncumulative	5		15							ppm
	Temperature Hysteresis of V _{OUT}	T = ±25° Hrs			10							ppm

TABLE 1A: ELECTRICAL CHARACTERISTICS (Postirradiation) (Note 6)

SYMBOL	PARAMETER	CONDITIONS	NOTES	10Kra MIN	nd(Si) MAX	20Kra Min	nd(Si) MAX	50Kr MIN	ad(Si) MAX	100Kra Min	ad(Si) MAX	200Ki Min	rad(Si) MAX	UNITS
V _{OUT}	Output Voltage	RH1021CM-5 RH1021BM-5, DM-5	1 1	4.9975 4.95	5.0025 5.05		5.005 5.055			4.9925 4.94	5.008 5.06	4.99 4.935	5.01 5.065	V
TCV _{OUT}	Output Voltage Temperature Coefficient	RH1021BM-5 RH1021CM-5, DM-5	2 2		5 20		5 20		5 20		7 22		10 25	ppm/°C ppm/°C
V _{OUT}	Line Regulation	7.2V V _{IN} 10V 10V V _{IN} 40V	3		12 6		12 6		13.5 6		15 7		18 9	ppm/V ppm/V
V _{OUT}	Load Regulation (Sourcing Current)	0 I _{OUT} 10mA	3,7		20		20		20		20		20	ppm/mA
	Load Regulation (Sinking Current)	0 I _{OUT} 10mA	3		100		100		100		100		150	ppm/mA
Is	Supply Current				1.2		1.2		1.2		1.2		1.2	mA



TABLE 1A: ELECTRICAL CHARACTERISTICS (Postirradiation) (Note 6)

Note 1: Output voltage is measured immediately after turn-on. Changes due to chip warm-up are typically less than 0.005%.

Note 2: Temperature coefficient is measured by dividing the change in output voltage over the temperature range by the change in temperature. Separate tests are done for hot and cold; T_{MIN} to 25°C and 25°C to T_{MAX} . Incremental slope is also measured at 25°C.

Note 3: Line and load regulation are measured on a pulse basis. Output changes due to die temperature change must be taken into account separately. Package thermal resistance is 150°C/W for the TO-5 (H) package.

Note 4: RMS noise is measured with a 2-pole highpass filter at 10Hz and a 2-pole lowpass filter at 1kHz. The resulting output is full wave rectified and

then integrated for a fixed period, making the final reading an average as opposed to RMS. Correction factors are used to convert from average to RMS and to correct for the nonideal bandpass of the filters. Peak-to-peak noise is measured with a single highpass filter at 0.1Hz and a 2-pole lowpass filter at 10Hz. The unit is enclosed in a still-air environment to eliminate thermocouple effects on the leads. Test time is 10 seconds.

Note 5: Consult factory for units with long term stability data.

Note 6: $V_{IN} = 10V$, $I_{OUT} = 0$, $T_A = 25$ °C, unless otherwise noted.

Note 7: I_{OUT(MAX)} (Sourcing) is 5mA for exposures greater than 100Krad (Si).

Note 8: $V_{IN} = 10V$, $I_{OUT} = 0$, unless otherwise noted.

TABLE 2: ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUP
Final Electrical Test Requirements (Method 5004)	1*,2,3,4
Group A Test Requirements (Method 5005)	1,2,3,4
Group B and D for Class S, and Group C and D for Class B	1
End Point Electrical Parameters (Method 5005)	

^{*} PDA Applies to subgroup 1. See PDA Test Notes.

PDA Test Notes

The PDA is specified as 5% based on failures from group A, subgroup 1, tests after cooldown as the final electrical test in accordance with method 5004 of MIL-STD-883. The verified failures of group A, subgroup 1, after burn-in divided by the total number of devices submitted for burn-in in that lot shall be used to determine the percent for the lot.

Linear Technology Corporation reserves the right to test to tighter limits than those given.

TOTAL DOSE BIAS CIRCUIT





TYPICAL PERFORMANCE CHARACTERISTICS

